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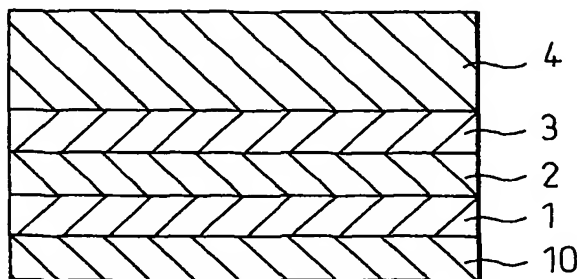
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(54) Title: GROUP-III NITRIDE SEMICONDUCTOR DEVICE



of $\text{Al}_{x_2}\text{Ga}_{1-x_2}\text{N}$ ($0 < x_2 < 1$ and $x_1 + 0.02 < x_2$) which is provided on the second nitride semiconductor layer.

(57) Abstract: An object of the present invention is to provide a Group III nitride semiconductor element which comprises a thick AlGaIn layer exhibiting high crystallinity and containing no cracks, and which does not include a thick GaN layer (which generally serves as a light-absorbing layer in an ultraviolet LED). The inventive Group III nitride semiconductor element comprises a substrate; a first nitride semiconductor layer composed of AlN which is provided on the substrate; a second nitride semiconductor layer composed of $\text{Al}_{x_1}\text{Ga}_{1-x_1}\text{N}$ ($0 < x_1 < 1$) which is provided on the first nitride semiconductor layer; and a third nitride semiconductor layer composed